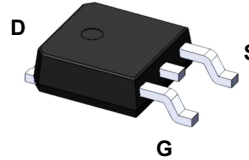
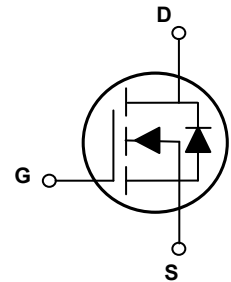


Main Product Characteristics

| | |
|---------------|----------------------|
| $V_{(BR)DSS}$ | 700V |
| $R_{DS(ON)}$ | 0.42 Ω (Max.) |
| I_D | 11A |



TO-252 (DPAK)



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSJD70R420 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------------|---------------------------|
| Drain-Source Voltage | V_{DS} | 700 | V |
| Gate-to-Source Voltage | V_{GS} | ± 30 | V |
| Continuous Drain Current, @ Steady-State ($T_C=25^\circ\text{C}$) | I_D | 11 | A |
| Continuous Drain Current, @ Steady-State ($T_C=100^\circ\text{C}$) | | 7.0 | A |
| Pulsed Drain Current | I_{DM} | 44 | A |
| Power Dissipation ($T_C=25^\circ\text{C}$) | P_D | 130 | W |
| | | 1.04 | W/ $^\circ\text{C}$ |
| Single Pulse Avalanche Energy ¹ | E_{AS} | 576 | mJ |
| Body Diode Reverse Voltage Slope ² | dv/dt | 15 | V/ns |
| MOS dv/dt Ruggedness ³ | dv/dt | 50 | V/ns |
| Junction-to-Ambient (PCB Mounted, Steady-State) | $R_{\theta JA}$ | 62.5 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.96 | $^\circ\text{C}/\text{W}$ |
| Operating Junction and Storage Temperature Range | T_J/T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---|---------------|---|------|------|------|----------|
| On / Off Characteristics | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=250\mu A$ | 700 | - | - | V |
| Drain-to-Source Leakage Current | I_{DSS} | $V_{DS}=700V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-to-Source Forward Leakage | I_{GSS} | $V_{DS}=0V, V_{GS}=30V$ | - | - | 100 | nA |
| | | $V_{DS}=0V, V_{GS}=-30V$ | - | - | -100 | |
| Static Drain-to-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=5.5A$ | - | 0.37 | 0.42 | Ω |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 2.0 | - | 4.0 | V |
| Dynamic and Switching Characteristics | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS}=0V, V_{DS}=100V, f=1MHz$ | - | 673 | - | pF |
| Output Capacitance | C_{oss} | | - | 37 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 2.3 | - | |
| Total Gate Charge ^{4,5} | Q_g | $I_D=11A, V_{DD}=560V, V_{GS}=10V$ | - | 24 | - | nC |
| Gate-to-Source Charge ^{4,5} | Q_{gs} | | - | 5.2 | - | |
| Gate-to-Drain ("Miller") Charge ^{4,5} | Q_{gd} | | - | 12 | - | |
| Turn-On Delay Time ^{4,5} | $t_{d(on)}$ | $V_{DD}=350V, V_{GS}=10V, R_G=24\Omega, I_D=11A$ | - | 14 | - | nS |
| Rise Time ^{4,5} | t_r | | - | 37 | - | |
| Turn-Off Delay Time ^{4,5} | $t_{d(off)}$ | | - | 70 | - | |
| Fall Time ^{4,5} | t_f | | - | 33 | - | |
| Gate Resistance | R_g | $f=1MHz$ | - | 4.7 | - | Ω |
| Source-Drain Ratings and Characteristics | | | | | | |
| Continuous Source Current (Body Diode) | I_S | $T_C=25^\circ\text{C}$, MOSFET symbol showing the integral reverse p-n junction diode. | - | - | 11 | A |
| Source Pulse Current | I_{SM} | | - | - | 44 | A |
| Diode Forward Voltage | V_{SD} | $I_S=11A, V_{GS}=0V$ | - | - | 1.4 | V |
| Reverse Recovery Time ³ | T_{rr} | $I_F=11A, V_{GS}=0V, di_F/dt=100A/\mu s$ | - | 374 | - | nS |
| Reverse Recovery Charge ³ | Q_{rr} | | - | 3.9 | - | μC |

Notes:

1. $L=79mH, I_{AS}=3.5A, V_{DD}=100V$, starting temperature $T_J=25^\circ\text{C}$.
2. $V_{DS}=0-400V, I_{SD} \leq 11A, T_J=25^\circ\text{C}$.
3. $V_{DS}=0-480V$.
4. Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

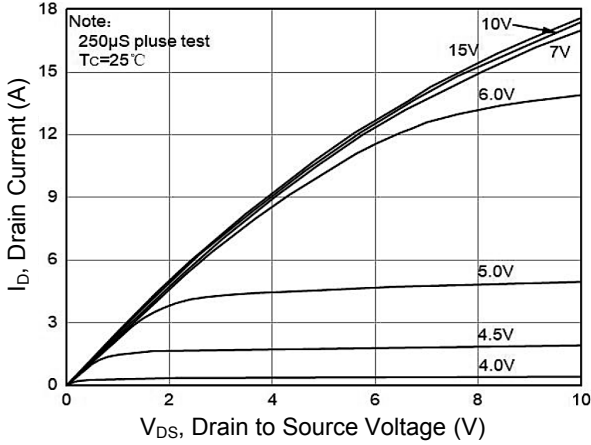


Figure 1. Typical Output Characteristics

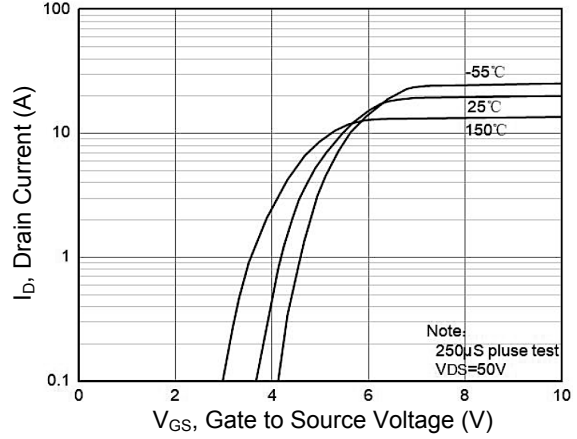


Figure 2. Transfer Characteristics

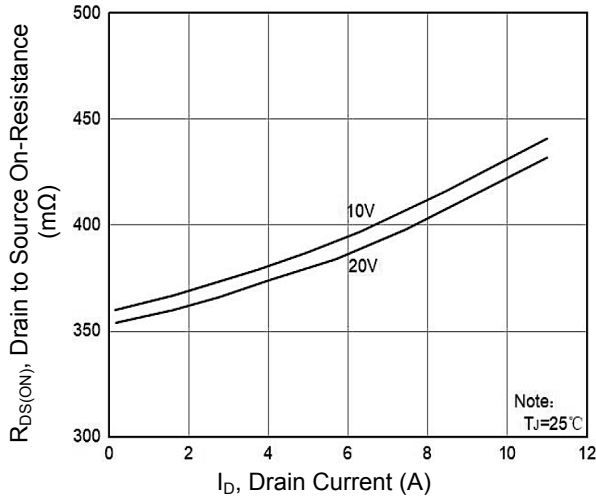


Figure 3. R_{DS(ON)} vs. Drain Current

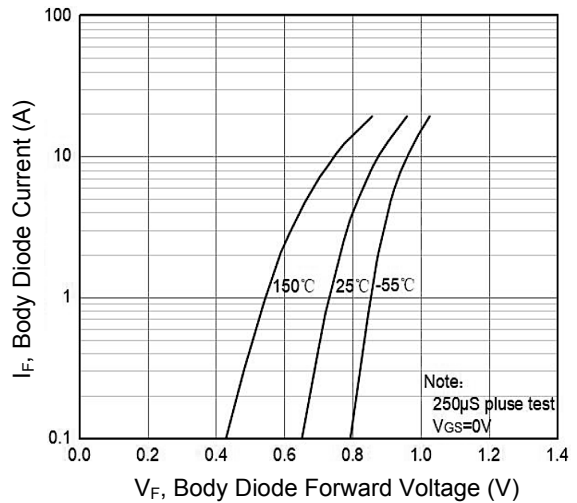


Figure 4. Body Diode Characteristic

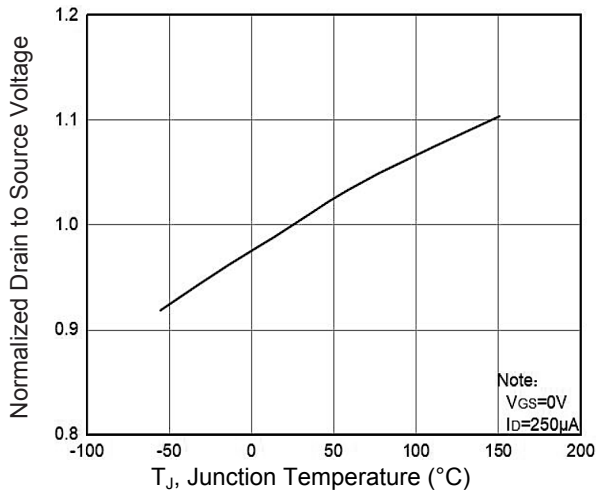


Figure 5. Normalized BV_{DSS} vs. T_J

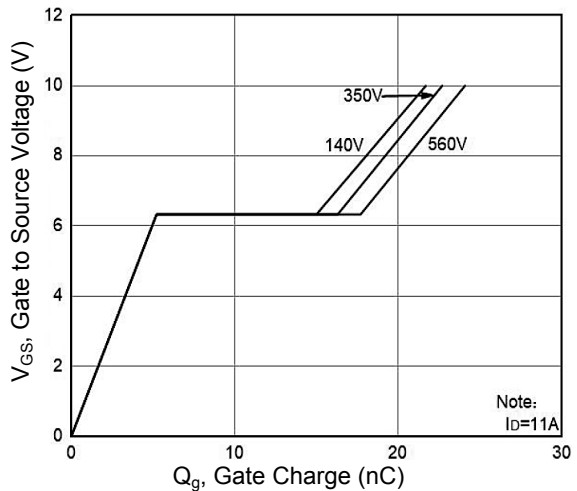


Figure 6. Gate Charge

Typical Electrical and Thermal Characteristic Curves

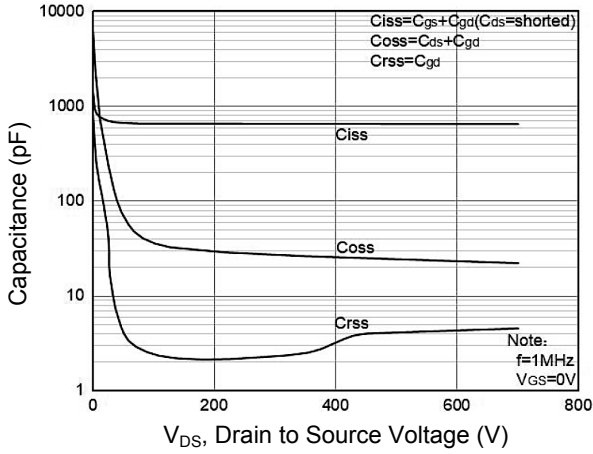


Figure 7. Capacitance Characteristic

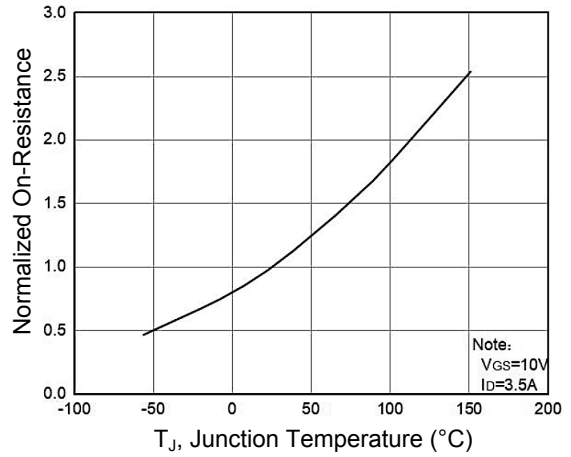


Figure 8. Normalized $R_{DS(ON)}$ vs. T_J

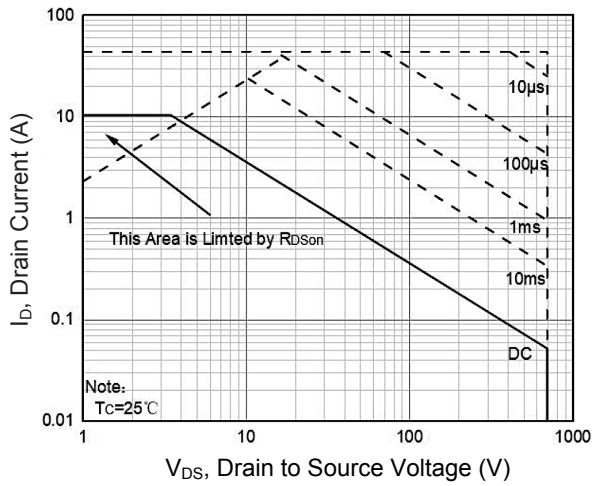
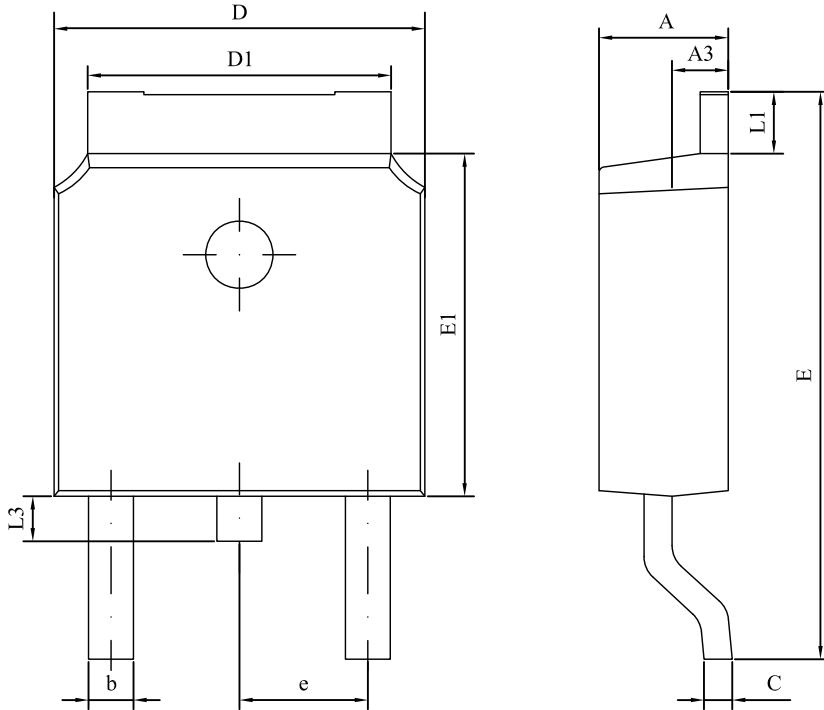


Figure 9. Safe Operation Area

Package Outline Dimensions TO-252 (DPAK)



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.15 | 2.40 | 0.085 | 0.094 |
| A3 | 0.90 | 1.10 | 0.035 | 0.043 |
| b | 0.50 | 0.90 | 0.020 | 0.035 |
| C | 0.40 | 0.65 | 0.016 | 0.026 |
| D | 6.30 | 6.90 | 0.248 | 0.272 |
| D1 | 4.95 | 5.50 | 0.195 | 0.217 |
| E | 9.40 | 10.41 | 0.370 | 0.410 |
| E1 | 5.90 | 6.30 | 0.232 | 0.248 |
| e | 2.286 BSC | | 0.090 BSC | |
| L1 | 0.89 | 1.27 | 0.035 | 0.050 |
| L3 | 0.60 | 1.10 | 0.024 | 0.043 |

Order Information

| Device | Package | Marking | Packaging | SPQ |
|------------|---------------|---------|-------------|------------------|
| GSJD70R420 | TO-252 (DPAK) | D70R420 | Tape & Reel | 2,500 Pcs / Reel |

For more information, please contact us at: inquiry@goodarksemi.com